



Integrated Device Technology, Inc.
6024 Silver Creek Valley Road, San Jose, CA - 95138

PRODUCT/PROCESS CHANGE NOTICE (PCN)

PCN #: A1508-03 DATE: 11-Sep-2015 Product Affected: 6.0mm x 6.0mm VFQFPN-36 Refer to Attachment II for the affected part numbers Date Effective: 11-Dec-2015	MEANS OF DISTINGUISHING CHANGED DEVICES: <input type="checkbox"/> Product Mark Lot # will have: <input checked="" type="checkbox"/> Back Mark "RC" prefix for ASECL, Taiwan <input type="checkbox"/> Date Code <input type="checkbox"/> Other
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Contact: IDT PCN DESK E-mail: pcndesk@idt.com	Attachment: <input checked="" type="checkbox"/> Yes <input type="checkbox"/> No Samples: Please contact your local sales representative for sample request.
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DESCRIPTION AND PURPOSE OF CHANGE:

<input type="checkbox"/> Die Technology <input type="checkbox"/> Wafer Fabrication Process <input type="checkbox"/> Assembly Process <input type="checkbox"/> Equipment <input type="checkbox"/> Material <input type="checkbox"/> Testing <input checked="" type="checkbox"/> Manufacturing Site <input type="checkbox"/> Data Sheet <input type="checkbox"/> Other	<p>This notification is to advise our customers that IDT is adding ASECL, Taiwan as the alternate Assembly facility.</p> <p>There is no change to the moisture performance.</p> <p>Attachment I details the qualification data for this change and Attachment II shows the affected list of part numbers.</p>
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RELIABILITY/QUALIFICATION SUMMARY:
Refer to qualification data shown in Attachment I.

CUSTOMER ACKNOWLEDGMENT OF RECEIPT:
 IDT records indicate that you require written notification of this change. Please use the acknowledgement below or E-Mail to grant approval or request additional information. If IDT does not receive acknowledgement within 30 days of this notice it will be assumed that this change is acceptable.
 IDT reserves the right to ship either version manufactured after the process change effective date until the inventory on the earlier version has been depleted.

Customer: _____	<input type="checkbox"/> <i>Approval for shipments prior to effective date.</i>
Name/Date: _____	E-Mail Address: _____
Title: _____	Phone# /Fax# : _____

CUSTOMER COMMENTS: _____

IDT ACKNOWLEDGMENT OF RECEIPT:
 RECD. BY: _____ DATE: _____



PRODUCT/PROCESS CHANGE NOTICE (PCN)

ATTACHMENT I - PCN # : A1508-03

PCN Type: Manufacturing Site - Alternate Assembly Location

Data Sheet Change: None

No change in moisture sensitivity level (MSL)

Detail Of Change:

This notification is to advise our customers that IDT is adding ASECL, Taiwan as the alternate Assembly facility.

The material set details of the current and alternate assembly location is as shown in Table 1. The die attach and mold compound used at the alternate assembly are qualified IDT materials. There is no change from the existing qualified lead frame material and lead finish for the alternate assembly location.

There is no change to the moisture performance.

Table 1: Assembly Material Sets for The Existing and Alternate Assembly Location

	Existing Assembly (Amkor, Korea)	Alternate Assembly (ASECL, Taiwan)
Die Attach	CRM1085A	EN4900G
Wire	Au wire	PdCu wire
Mold Compound	G631BQF	G700LA



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ATTACHMENT I - PCN # : A1508-03

Qualification Information and Qualification Data:

Affected Packages: VFQFPN-36

Assembly Material: The affected package type is using ASECL standard materials shown on page 2 of this attachment.

Qual Plan & Results: Tests are in accordance with JEDEC47 recommended tests.

Qualification Vehicle: VFQFPN-32 (3 lots) with material sets as shown in page 2

Test Description	Test Method	Test Results (SS / Rej)		
		Lot 1	Lot 2	Lot 3
* HAST - biased (130 °C/85% RH, 96 Hrs)	JESD22-A110	25/0	25/0	25/0
* Temperature Cycle / Condition B (-55 °C to +125 °C, 700 Cyc)	JESD22-A104	25/0	25/0	25/0
High Temp. Storage Test (150 °C, 1000 Hrs)	JESD22-A103	25/0	25/0	25/0

Note:

* Test requires moisture pre-conditioning sequence per JESD22-A113 prior to stress test



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ATTACHMENT II - PCN # : A1508-03

Affected Part Numbers

Part Number	Part Number	Part Number	Part Number
F1300NBGI	F1358NBGI	F1320NBGI8	F1375NBGI8
F1375NBGI	F1325NBGI8	F1320NBGI	
F1358NBGI8	F1325NBGI	F1300NBGI8	

		Current Site	Alternate Site
	Pkg and Si Attribute	Amkor Korea	ASECL Taiwan
Pkg	Pkg type	NBG36	NBG36
	Pkg x & y (mm)	6.0 mm x 6.0 mm	same
	Pkg z (mm)	0.8 mm	same
	Max Voltage	NA	NA
	Capacitors	NA	NA
Silicon & FLI	Si Process	No change	No change same wafer
	Wafer Size	No change	No change same wafer
	Die size (mm2)	No change	No change same wafer
	Die Aspect Ratio	No change	No change same wafer
	Die thickness (mils)	No change	No change same wafer
	Polyimide (Y/N)	No change	No change same wafer
	Silicon Metal Layers	No change	No change same wafer
	Scribe Width (um)	No change	No change same wafer
	UBM source	No change	No change same wafer
	Silicon UBM Stack-up	No change	No change same wafer
	Bump source	No change	No change same wafer
	Bump pitch	No change	No change same wafer
	I/O & Core (um)	No change	No change same wafer
	Total Bump count	No change	No change same wafer
	Bump Diameter	No change	No change same wafer
	Bump Height	No change	No change same wafer
	Bump Metallurgy	No change	No change same wafer
	Wafer Bump Flux	No change	No change same wafer
	CAM Flux	No change	No change same wafer
Underfill Material	No change	No change same wafer	
Silicon UBM/SRO	No change	No change same wafer	
Substrate	Halogen Free ?	NA	NA
	Substrate Layers	NA	NA
	Substrate thickness	NA	NA
	Core thickness (um)	NA	NA
	Core Material	NA	NA
	Outer layer Lines/space (um)	NA	NA
	Bump Pre-solder (SOP)	NA	NA
	Bump presolder (SOP) height/diameter	NA	NA
	Bump Capture Pad/SRO IO (um)	NA	NA
	Substrate Ball Capture Pad/SRO (um)	NA	NA
	Number of PTH/M1-M2 uVias	NA	NA
	Core PTH/Capture pad (um)	NA	NA
	Substrate Design Rule & BOM	NA	NA
	Substrate Supplier	NA	NA
	Build up layer (thickness)	NA	NA
	Solder mask (thickness)	NA	NA
	C1 & C4 thickness (plate)	NA	NA
C2 & C3 thickness (foil + plate)	NA	NA	
Surface finish (thickness)	NA	NA	
SLI	2nd level Ball count	NA	NA
	2nd level BA Flux	NA	NA
	2nd Ball Dia (mm)	NA	NA
	2nd level metallurgy	NA	NA
	2nd level ball pitch (mm)	NA	NA